Kimberley Elcess

List of Publications by Year in descending order

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1163117 1372567 11 328 8 10 citations h-index g-index papers 11 11 11 155 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Modulation of the coupling of a near-surface GaAs/Ga0.7Al0.3As quantum well with its free surface. Superlattices and Microstructures, 1991, 9, 507-509.	3.1	4
2	Evidence for new optical transitions in short-period Si/Ge superlattices from electron-beam electroreflectance measurements., 1990, 1286, 320.		2
3	Strain mapping in [111] and [001] InGaAs/GaAs superlattices. Applied Physics Letters, 1990, 56, 286-288.	3.3	16
4	Comparison and spatial profiling of strain in [001]- and [111]-orientedInxGa1â^'xAs/GaAs superlattices from Raman and x-ray experiments. Physical Review B, 1990, 42, 3100-3108.	3.2	16
5	Near-surface GaAs/Ga0.7Al0.3As quantum wells: Interaction with the surface states. Physical Review B, 1990, 41, 12945-12948.	3.2	99
6	Cyclotron resonance in ã€^111〉-oriented InGaAs/AlGaAs strained layer superlattices. Surface Science, 1990, 228, 156-158.	1.9	1
7	Study of the optical properties of (100) and (111) oriented GalnAs/GaAs strained-layer superlattices. Superlattices and Microstructures, 1989, 5, 341-344.	3.1	12
8	Optical and infrared studies of [111] InGaAs/AlGaAs strained-layer superlattices. Superlattices and Microstructures, 1989, 5, 363-366.	3.1	11
9	Optical Properties of (100) - and (111)-Oriented GalnAs/GaAs Strained-Layer Superlattices. Physical Review Letters, 1989, 62, 649-652.	7.8	110
10	Growth and characterization of (111) oriented GalnAs/GaAs strainedâ€layer superlattices. Applied Physics Letters, 1989, 54, 233-235.	3.3	25
11	Growth of GaAs, AlGaAs, and InGaAs on (111)B GaAs by molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 638.	1.6	32